MCM72F6
MCM72F7

512KB and 1MB Synchronous Fast Static RAM Module

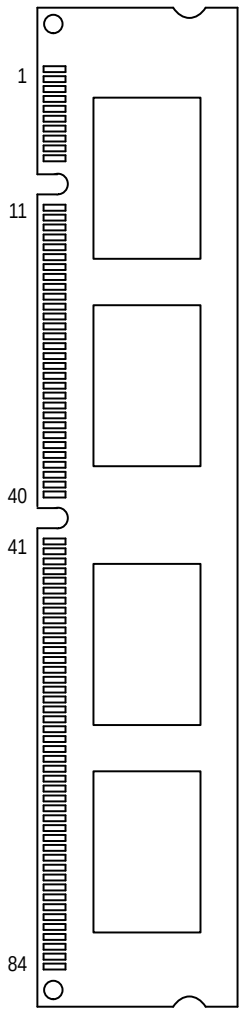
The MCM72F6 (512KB) is configured as 64K x 72 bits and the MCM72F7 (1MB) is configured as 128K x 72 bits. Both are packaged in a 168–pin dual–in–line memory module DIMM. Each module uses Motorola's 3.3 V 64K x 18 bit flow–through BurstRAMs.

Address (A), data inputs (DQ, DP), and all control signals except output enable (G) are clock (K) controlled through positive–edge–triggered noninverting registers.

Write cycles are internally self–timed and initiated by the rising edge of the clock (K) input. This feature provides increased timing flexibility for incoming signals. Synchronous byte write (W) allows writes to either individual bytes or to both bytes.

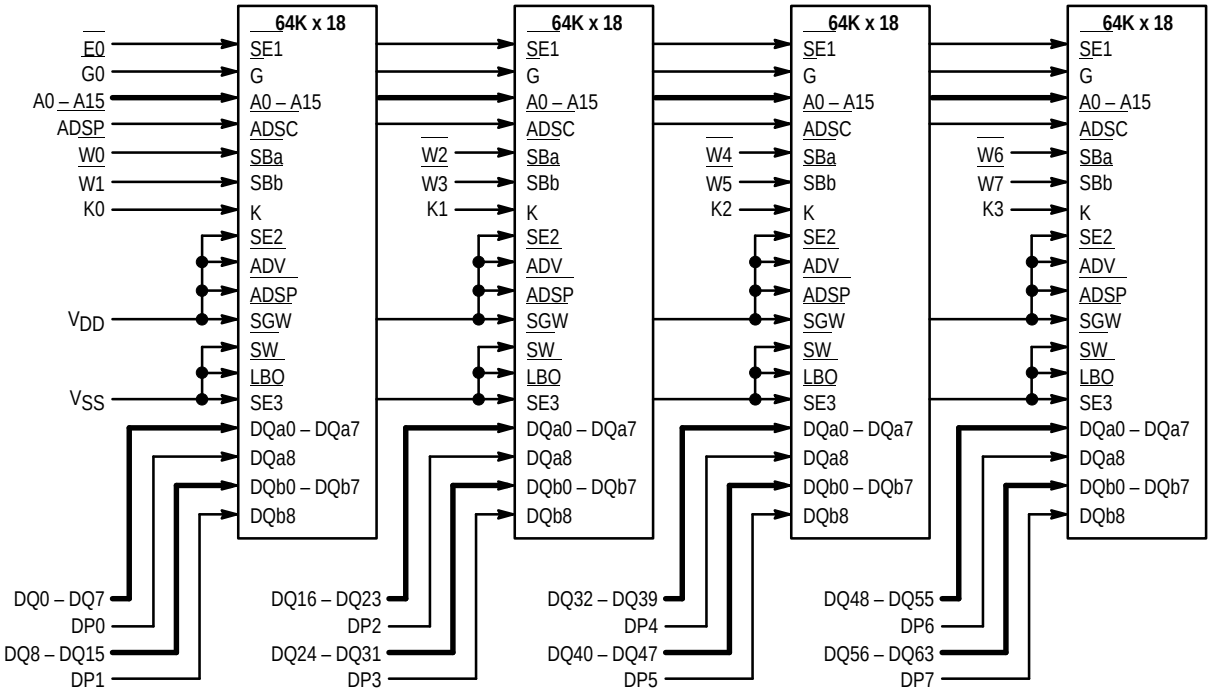
- Single 3.3 V + 10%, – 5% Power Supply
- Plug and Pin Compatibility with 2MB and 4MB
- Multiple Clock Pins for Reduced Loading
- All Inputs and Outputs are LVTTL Compatible
- Byte Write Capability
- Fast SRAM Access Times: 9/10/12 ns
- Decoupling Capacitors for Each Fast Static RAM
- High Quality Multi–Layer FR4 PWB With Separate Power and Ground Planes
- Amp Connector, Part Number: 390064–4
- 168–Pin DIMM Module

168–LEAD DIMM
CASE 1115J–01
TOP VIEW

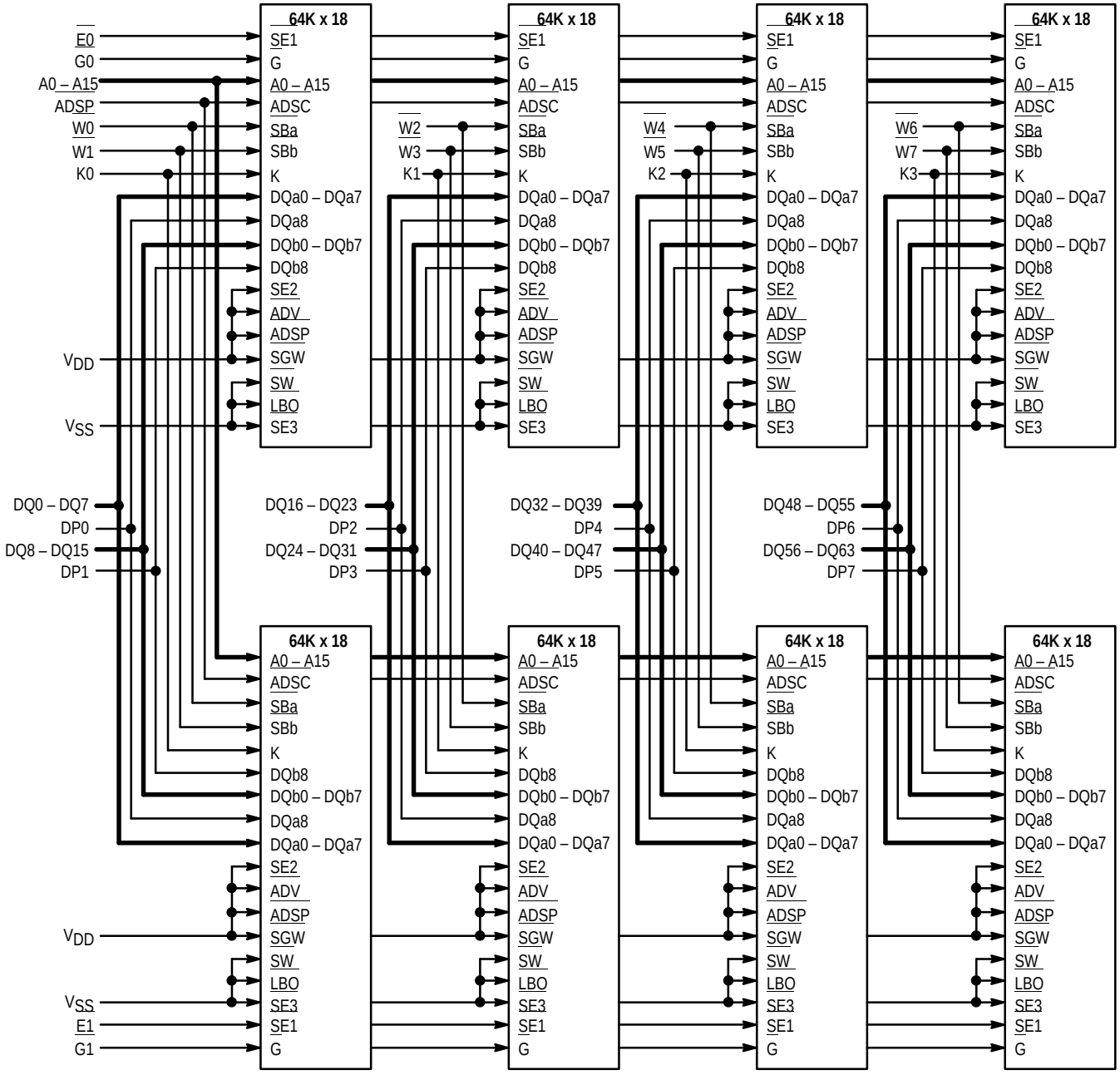


REV 3
11/24/97

MCM72F6 BLOCK DIAGRAM



MCM72F7 BLOCK DIAGRAM



PIN ASSIGNMENT
168–LEAD DIMM
TOP VIEW

V_{SS}	1	85	V_{SS}
DQ63	2	86	DP7
DQ62	3	87	DQ61
V_{DD}	4	88	V_{SS}
DQ60	5	89	DQ59
DQ58	6	90	DQ57
V_{SS}	7	91	V_{SS}
DQ56	8	92	DP6
DQ55	9	93	DQ54
V_{SS}	10	94	V_{DD}
DQ53	11	95	DQ52
DQ51	12	96	DQ50
V_{SS}	13	97	V_{SS}
DQ49	14	98	DQ48
DP5	15	99	DQ47
V_{DD}	16	100	V_{SS}
DQ46	17	101	DQ45
DQ44	18	102	DQ43
V_{SS}	19	103	V_{SS}
DQ42	20	104	DQ41
DQ40	21	105	DP4
V_{SS}	22	106	V_{DD}
DQ39	23	107	DQ38
DQ37	24	108	DQ36
V_{SS}	25	109	V_{SS}
DQ35	26	110	DQ34
DQ33	27	111	DQ32
V_{SS}	28	112	V_{SS}
K3	29	113	K2
V_{SS}	30	114	V_{SS}
DP3	31	115	DQ31
DQ30	32	116	DQ29
V_{DD}	33	117	V_{SS}
DQ28	34	118	DQ27
DQ26	35	119	DQ25
V_{SS}	36	120	V_{SS}
DQ24	37	121	DP2
DQ23	38	122	DQ22
V_{SS}	39	123	V_{DD}
DQ21	40	124	DQ20
DQ19	41	125	DQ18
V_{SS}	42	126	V_{SS}
DQ17	43	127	DQ16
DP1	44	128	DQ15
V_{DD}	45	129	V_{SS}
DQ14	46	130	DQ13
DQ12	47	131	DQ11
V_{SS}	48	132	V_{SS}
DQ10	49	133	DQ9
DQ8	50	134	DP0
V_{SS}	51	135	V_{DD}
DQ7	52	136	DQ6
DQ5	53	137	DQ4
V_{SS}	54	138	V_{SS}
DQ3	55	139	DQ2
DQ1	56	140	DQ0
V_{DD}	57	141	V_{SS}
NC	58	142	NC
NC	59	143	NC
V_{SS}	60	144	V_{SS}
NC	61	145	A15
A14	62	146	A13
V_{SS}	63	147	V_{DD}
A12	64	148	A11
A10	65	149	A9
V_{SS}	66	150	V_{SS}
A8	67	151	A7
A6	68	152	A5
V_{DD}	69	153	V_{SS}
A4	70	154	A3
A2	71	155	$\overline{A1}$
A0	72	156	ADSP
V_{SS}	73	157	V_{SS}
K1	74	158	K0
V_{SS}	75	159	V_{SS}
$\overline{W7}$	76	160	$\overline{W6}$
W5	77	161	W4
V_{SS}	78	162	V_{SS}
$\overline{W3}$	79	163	$\overline{W2}$
W1	80	164	W0
V_{SS}	81	165	V_{DD}
$\overline{G1}$	82	166	$\overline{G0}$
E1	83	167	E0
V_{SS}	84	168	V_{SS}

PIN DESCRIPTIONS

Pin Locations	Symbol	Type	Description
62, 64, 65, 67, 68, 70, 71, 72, 145, 146, 148, 149, 151, 152, 154, 155	A0 – A15	Input	Synchronous Address Inputs: These inputs are registered and must meet setup and hold times.
156	ADSP	Input	Synchronous Addresss Status Controller: Initiates read, write, or chip deselect cycle.
15, 31, 44, 86, 92, 105, 121, 134	DP0 – DP7		Synchronous Parity Data Inputs/Outputs.
2, 3, 5, 6, 8, 9, 11, 12, 14, 17, 18, 20, 21, 23, 24, 26, 27, 32, 34, 35, 37, 38, 40, 41, 43, 46, 47, 49, 50, 52, 53, 55, 56, 87, 89, 90, 93, 95, 96, 98, 99, 101, 102, 104, 107, 108, 110, 111, 115, 116, 118, 119, 122, 124, 125, 127, 128, 130, 131, 133, 136, 137, 139, 140	DQ0 – DQ63	I/O	Synchronous Data Inputs/Outputs.
167, 83	E0, E1	Input	Synchronous Chip Enable: Active low to enable chip. Negated high — blocks ADSP or deselects chip when ADSC is asserted. E1 is only used on 1MB module.
166, 82	$\overline{G}$0, $\overline{G}$1	Input	Asynchronous Output Enable Input: Low — enables output buffer. High — DQx pins are high impedance. G1 is only used on 1MB module.
29, 74, 113, 158	K0 – K3	Input	Clock: This signal registers the address, data in, and all control signals except G and LBO.
76, 77, 79, 80, 160, 161, 163, 164	W0 – W7	Input	Synchronous Byte Write Inputs: x refers to the byte being written (byte a, b). SGW overrides SBx.
4, 16, 33, 45, 57, 69, 94, 106, 123, 135, 147, 165	V_{DD}	Supply	Power Supply: 3.3 V + 10%, – 5%. Must be connected on all modules.
1, 7, 10, 13, 19, 22, 25, 28, 30, 36, 39, 42, 48, 51, 54, 60, 63, 66, 73, 75, 78, 81, 84, 85, 88, 91, 97, 100, 103, 109, 112, 114, 117, 120, 126, 129, 132, 138, 141, 144, 150, 153, 157, 159, 162, 168	V_{SS}	Supply	Ground.
58, 59, 61, 142, 143	NC		No Connection: There is no connection to the chip.

DATA RAM MCM69F618A SYNCHRONOUS TRUTH TABLE (See Notes 1, 2, 3 and 4)

Next Cycle	Address Used	$\overline{E}$	$\overline{ADSP}$	$\overline{G}$	DQx	WRITE
Deselect	None	1	0	X	High–Z	X
Begin Read	External Address	0	0	0	DQ	Read
Read	Current	X	1	1	High–Z	Read
Read	Current	X	1	0	DQ	Read
Begin Write	External	0	0	X	High–Z	Write
Write	Current	X	1	X	High–Z	Write

NOTES:
1. X = don't care, 1 = logic high, 0 = logic low.
2. Write is defined as any Wx low.
3. G is an asynchronous signal and is not sampled by the clock K. $\overline{G}$ drives the bus immediately (t_{GLQX}) following $\overline{G}$ going low.
4. On write cycles that follow read cycles, $\overline{G}$ must be negated prior to the start of the write cycle to ensure proper write data setup times. $\overline{G}$ must also remain negated at the completion of the write cycle to ensure proper write data hold times.

ABSOLUTE MAXIMUM RATINGS (Voltages Referenced to V_{SS} = 0 V)

Rating		Symbol	Value	Unit
Power Supply Voltage		V_{DD}	– 0.5 to + 4.6	V
Voltage Relative to V_{SS}		V_{in}, V_{out}	– 0.5 to V_{DD} + 0.5	V
Output Current (per I/O)		I_{out}	± 20	mA
Power Dissipation	MCM72F6 MCM72F7	P_D	4.6 9.2	W
Ambient Temperature		T_A	0 to 70	°C
Die Temperature		T_J	110	°C
Temperature Under Bias		T_{bias}	– 10 to + 85	°C
Storage Temperature		T_{stg}	– 55 to + 125	°C

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPERATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high–impedance circuit.

This BiCMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established.

This device contains circuitry that will ensure the output devices are in High–Z at power up.

DC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{DD} = 3.3 V + 10%, – 5%, T_A = 0 to 70°C, Unless Otherwise Noted)

RECOMMENDED OPERATING CONDITIONS (Voltages Referenced to V_{SS} = 0 V)

Parameter	Symbol	Min	Max	Unit
Supply Voltage (Operating Voltage Range)	V_{DD}	3.135	3.6	V
Input High Voltage	V_{IH}	2.0	V_{DD} + 0.3	V
Input Low Voltage	V_{IL}	– 0.5*	0.8	V

* $V_{IL} \geq$ – 2.0 V for $t \leq t_{KHKH}/2$.

DC CHARACTERISTICS

Parameter	Symbol	Min	Max	Unit
Input Leakage Current (0 V ≤ V_{in} ≤ V_{DD})	$I_{lkg(I)}$	—	± 1.0	µA
Output Leakage Current (0 V ≤ V_{in} ≤ V_{DD})	$I_{lkg(O)}$	—	± 1.0	µA
Output Low Voltage (I_{OL} = + 8.0 mA)	V_{OL}	—	0.4	V
Output High Voltage (I_{OH} = – 4.0 mA)	V_{OH}	2.4	—	V

POWER SUPPLY CURRENTS

Parameter		Symbol	Min	Max	Unit
AC Supply Current (Device Selected, All Outputs Open, Cycle Time ≥ t_{KHKH} min)	MCM72F6DG9 MCM72F6DG10 MCM72F6DG12 MCM72F7DG9 MCM72F7DG10 MCM72F7DG12	I_{DDA}	—	900 860 840 1800 1720 1680	mA
CMOS Standby Supply Current (Deselected, Clock (K) Cycle Time ≥ t_{KHKH}, All Inputs Toggling at CMOS Levels $V_{in} \leq V_{SS}$ + 0.2 V or ≥ V_{DD} – 0.2 V)	MCM72F6DG9 MCM72F6DG10 MCM72F6DG12 MCM72F7DG9 MCM72F7DG10 MCM72F7DG912	I_{SB1}	—	440 400 380 880 800 760	mA
Clock Running Supply Current (Deselected, Clock (K) Cycle Time ≥ t_{KHKH}, All Other Inputs Held to Static CMOS Levels $V_{in} \leq V_{SS}$ + 0.2 V or ≥ V_{DD} – 0.2 V)	MCM72F6DG9 MCM72F6DG10/12 MCM72F7DG9 MCM72F7DG10/12	I_{SB2}	—	160 140 320 280	mA

MCM72F6 CAPACITANCE (f = 1.0 MHz, dV = 3.0 V, T_A = 0 to 70°C, Periodically Sampled Rather Than 100% Tested)

Parameter		Symbol	Typ	Max	Unit
Input Capacitance	W, K Other Inputs	C_{in}	— —	16 36	pF
I/O Capacitance		$C_{I/O}$	—	19	pF

MCM72F7 CAPACITANCE (f = 1.0 MHz, dV = 3.0 V, T_A = 0 to 70 °C, Periodically Sampled Rather Than 100% Tested)

Parameter		Symbol	Typ	Max	Unit
Input Capacitance	W, K	C_{in}	—	22	pF
	E, G		—	36	
	Other Inputs		—	60	
I/O Capacitance		$C_{I/O}$	—	28	pF

MASS (Periodically Sampled Rather Than 100% Tested)

Parameter	Max	Unit
MCM72F6	16	g
MCM72F7	20	g

AC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{DD} = 3.3 V + 10%, – 5%, T_A = 0 to 70°C, Unless Otherwise Noted)

Input Timing Measurement Reference Level . . . . . 1.5 V
Input Pulse Levels . . . . . 0 to 3.0 V
Input Rise/Fall Time . . . . . 1 V/ns (20 to 80%)

Output Timing Reference Level . . . . . 1.5 V
Output Load . . . . . See Figure 1 Unless Otherwise Noted

DATA RAMs READ/WRITE CYCLE TIMING (See Notes 1, 2, 3 and 4)

Parameter	Symbol	MCM72F6–9 MCM72F7–9		MCM72F6–10 MCM72F7–10		MCM72F6–12 MCM72F7–12		Unit	Notes
		Min	Max	Min	Max	Min	Max		
Cycle Time	t_{KHKH}	12	—	15	—	16.6	—	ns	
Clock Access Time	t_{KHQV}	—	9	—	10	—	12	ns	
Output Enable to Output Valid	t_{GLQV}	—	5	—	5	—	6	ns	
Clock High to Output Active	t_{KHQX1}	0	—	0	—	0	—	ns	5
Clock High to Output Change	t_{KHQX2}	3	—	3	—	3	—	ns	5
Output Enable to Output Active	t_{GLQX}	0	—	0	—	0	—	ns	5
Output Disable to Q–High–Z	t_{GHQZ}	—	5	—	5	—	6	ns	5, 6
Clock High to Q–High–Z	t_{KHQZ}	3	5	3	5	3	6	ns	5, 6
Clock High Pulse Width	t_{KHKL}	4	—	5	—	6	—	ns	
Clock Low Pulse Width	t_{KLKH}	4	—	5	—	6	—	ns	
Setup Times: Address	t_{AVKH}	2.5	—	2.5	—	2.5	—	ns	
ADSP	t_{ADKH}								
Data In	t_{DVKH}								
Write	t_{WVKH}								
Chip Enable	t_{EVKH}								
Hold Times: Address	t_{KHAX}	0.5	—	0.5	—	0.5	—	ns	
ADSP, ADSC, ADV	t_{KHADX}								
Data In	t_{KHDX}								
Write	t_{KHWX}								
Chip Enable	t_{KHEX}								

NOTES:
1. In setup and hold times, write refers to either any $\overline{SBx}$ and $\overline{SW}$ or $\overline{SGW}$ is low. $\overline{ADSP}$
2. Chip Enable is defined as SE1 low, SE2 high, and SE3 low whenever ADSP or ADSC is asserted.
3. All read and write cycle timings are referenced from K or G.
4. G is a don't care after write cycle begins. To prevent bus contention, $\overline{G}$ should be negated prior to start of write cycle.
5. This parameter is sampled and not 100% tested.
6. Measured at ± 200 mV from steady state.

TIMING LIMITS

The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time (even though most devices do not require it). On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

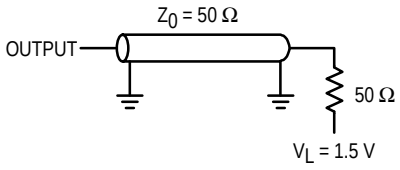
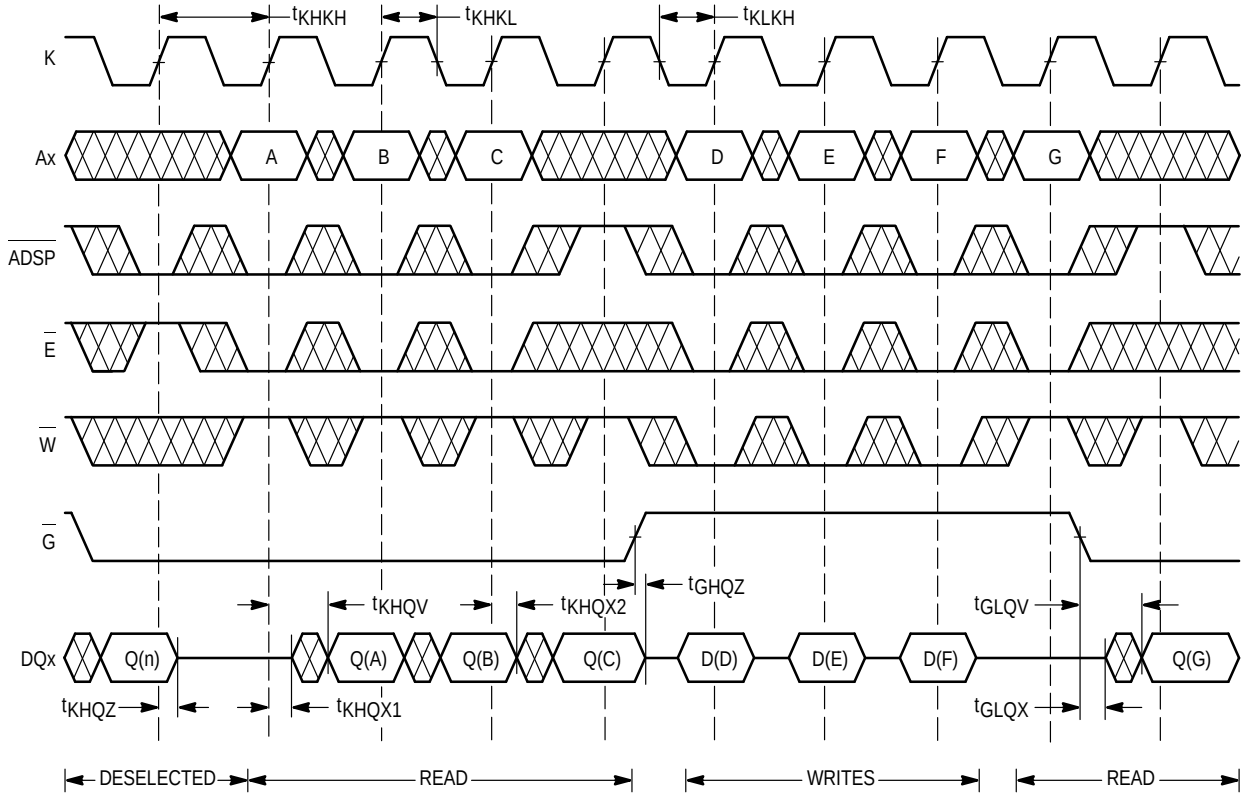


Figure 1. AC Test Load

READ/WRITE CYCLES



ORDERING INFORMATION

(Order by Full Part Number)

MCM 72F X XX XX

Motorola Memory Prefix — MCM

Part Number — 72F

Memory Size (6 = 512KB, 7 = 1 MB) — X

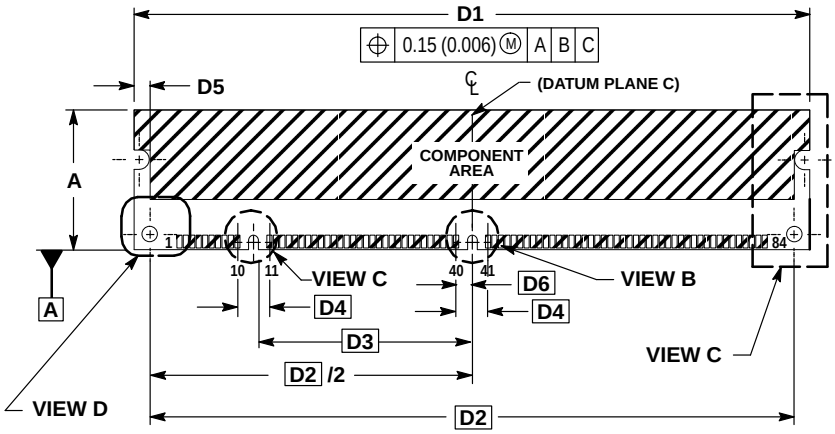
Package (DG = Gold Pad DIMM) — XX

Speed (9 = 9 ns, 10 = 10 ns, 12 = 12 ns) — XX

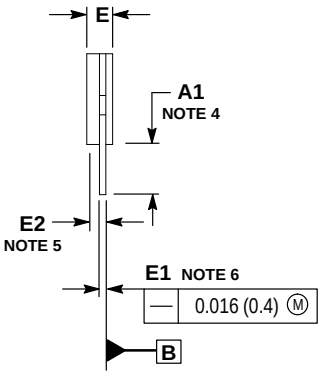
Full Part Numbers —			
	MCM72F6DG9	MCM72F6DG10	MCM72F6DG12
	MCM72F7DG9	MCM72F7DG10	MCM72F7DG12

PACKAGE DIMENSIONS

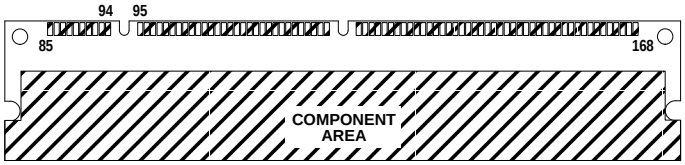
168–LEAD DIMM
CASE 1115J–01



FRONT VIEW

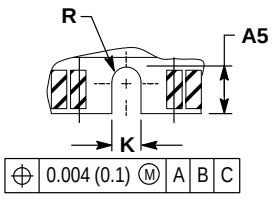


SIDE VIEW

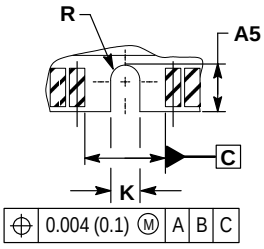


BACK VIEW

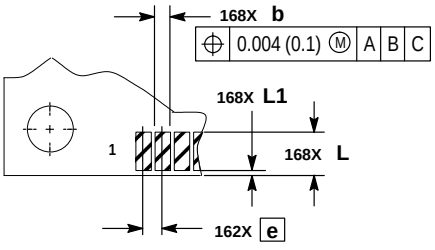
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.
3. CARD THICKNESS APPLIES ACROSS TABS AND INCLUDES PLATING AND/OR METALLIZATION.
4. DIMENSIONS E AND A1 DEFINE A DOUBLE–SIDED MODULE.
5. DIMENSION E2 DEFINES OPTIONAL SINGLE–SIDED MODULE
6. STRAIGHTNESS CALLOUT APPLIES TO TAB AREA ONLY.
7. D5 DIMENSION DEFINES SLOT END AND EDGE OF COMPONENT AREA.



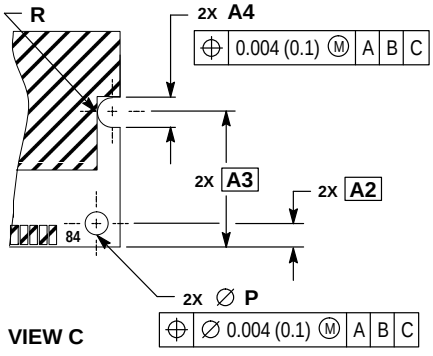
VIEW A



VIEW B



VIEW D



VIEW C

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.095	1.105	27.81	28.07
A1	0.390	—	9.90	—
A2	0.118 BSC		3.00 BSC	
A3	0.700 BSC		17.78 BSC	
A4	0.154	0.161	3.90	4.10
A5	0.118	0.128	3.00	3.25
b	0.037	0.041	0.95	1.05
D1	5.245	5.255	133.22	133.48
D2	5.014 BSC		127.35 BSC	
D3	1.700 BSC		43.18 BSC	
D4	0.250 BSC		6.35 BSC	
D5	0.118	—	3.00	—
D6	0.125 BSC		3.175 BSC	
e	0.050 BSC		1.27 BSC	
E	—	0.200	—	4.00
E1	0.046	0.054	1.17	1.37
E2	—	0.148	—	2.70
K	0.075	0.083	1.90	2.10
L	0.100	—	2.54	—
L1	—	0.010	—	0.25
P	0.114	0.122	2.90	3.10

How to reach us:

USA / EUROPE / Locations Not Listed: Motorola Literature Distribution;
P.O. Box 5405, Denver, Colorado, 80217. 1-303-675-2140 or 1-800-441-2447

Mfax™ : RMFAX0@email.sps.mot.com – TOUCHTONE 1-602-244-6609
Motorola Fax Back System – US & Canada ONLY 1-800-774-1848
– http://sps.motorola.com/mfax/

HOME PAGE : http://motorola.com/sps/

JAPAN: Nippon Motorola Ltd.: SPD, Strategic Planning Office, 141,
4-32-1 Nishi-Gotanda, Shagawa-ku, Tokyo, Japan. 03-5487-8488

ASIA / PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

CUSTOMER FOCUS CENTER: 1-800-521-6274